DMC56107

Silicon NPN epitaxial planar type

For digital circuits

■ Features

- \bullet High forward current transfer ratio h_{FE} with excellent linearity
- \bullet Low collector-emitter saturation voltage $V_{\text{CE(sat)}}$
- Contributes to miniaturization of sets, reduction of component count.
- Eco-friendly Halogen-free package

■ Basic Part Number

Dual DRC2124T (Common emitter)

Packaging

Embossed type (Thermo-compression sealing): 3000 pcs / reel (standard)

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V _{CBO}	50	V
Collector-emitter voltage (Base open)	V _{CEO}	50	V
Collector current	I_{C}	100	mA
Total power dissipation	P_{T}	150	mW
Junction temperature	T_j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Package

• Code

SMini5-F3-B

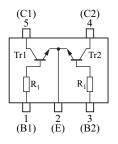
• Pin Name

1: Base (Tr1) 4: Collector (Tr2) 2: Emitter (Common) 5: Collector (Tr1)

3: Base (Tr2)

■ Marking Symbol: N5

■ Internal Connection



Resistance value	R_1	22	kΩ

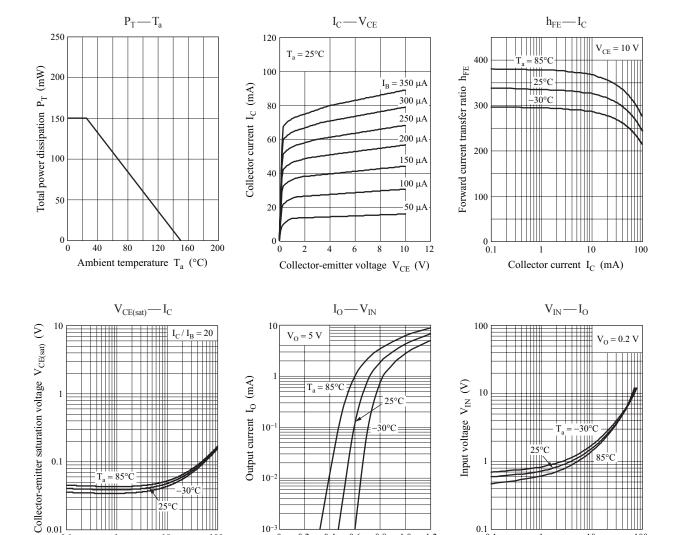
■ Electrical Characteristics $T_a = 25$ °C±3°C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = 10 \mu A, I_E = 0$	50			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = 2 \text{ mA}, I_B = 0$	50			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 50 \text{ V}, I_{E} = 0$			0.1	μΑ
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = 50 \text{ V}, I_{B} = 0$			0.5	μΑ
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = 6 \text{ V}, I_{C} = 0$			0.01	mA
Forward current transfer ratio	h_{FE}	$V_{CE} = 10 \text{ V}, I_{C} = 5 \text{ mA}$	160		460	_
h _{FE} ratio *	$\begin{array}{c} h_{FE} \\ \text{(Small/Large)} \end{array}$	$V_{CE} = 10 \text{ V}, I_{C} = 5 \text{ mA}$	0.50	0.99		_
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$			0.25	V
Input voltage (ON)	V _{I(on)}	$V_{CE} = 0.2 \text{ V}, I_{C} = 5 \text{ mA}$	1.8			V
Input voltage (OFF)	$V_{I(off)}$	$V_{CE} = 5 \text{ V}, I_{C} = 100 \mu\text{A}$			0.4	V
Input resistance	R_1		-30%	22	+30%	kΩ

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Ratio between 2 elements

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0.1 | 0.1

10

Output current IO (mA)

100

10-2

10-3 - 0

0.2 0.4 0.6 0.8

Input voltage V_{IN} (V)

ZJJ00704AED 2

10

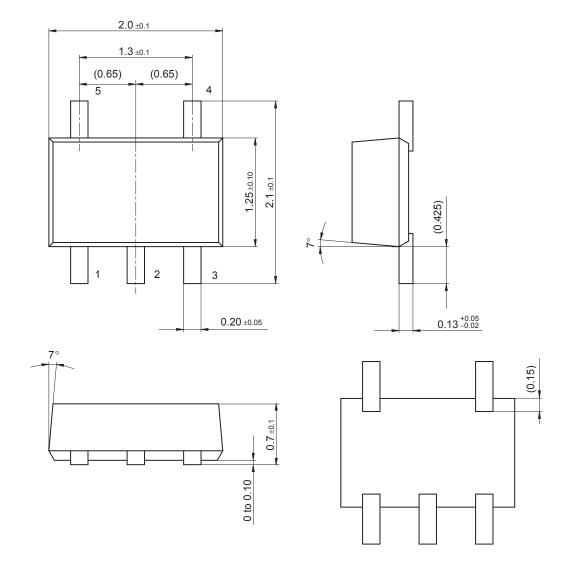
Collector current I_C (mA)

100

SMini5-F3-B

Unit: mm

DMC56107



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